

ABSTRACT OF THE DISCLOSURE

A semiconductor integrated device includes a boron containing
5 layer 4 containing an isotope ^{10}B formed on a semiconductor substrate
1. Neutrons irradiated to the boron containing layer 4 are brought
into a reaction with the isotope ^{10}B to emit α rays which are then rushed
into the semiconductor substrate 1 to generate electron - positive hole
pairs 8 in a P-N junction layer. Thus, neutrons are detected.

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